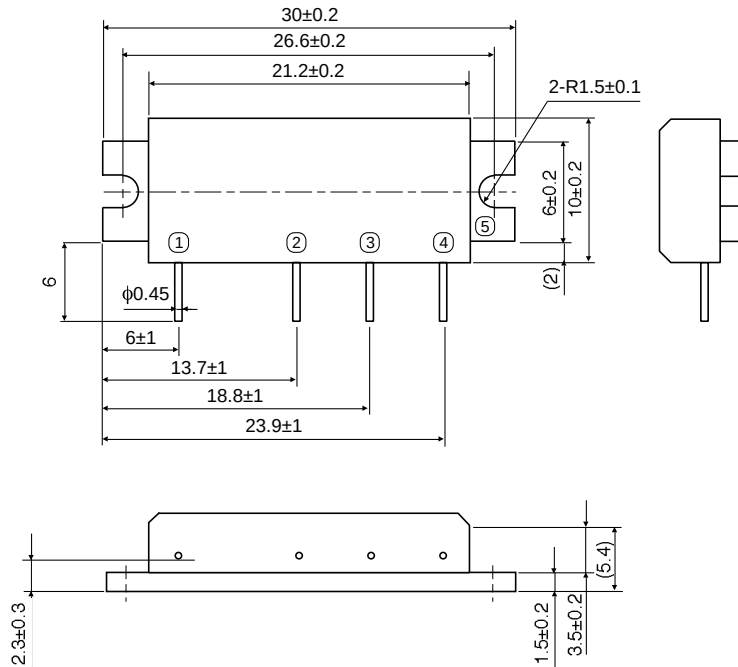


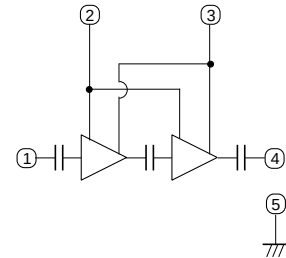
SILICON MOS FET POWER AMPLIFIER, 135-155MHz, 7W, FM PORTABLE RADIO

OUTLINE DRAWING

Dimensions in mm



BLOCK DIAGRAM



PIN:

①Pin : RF INPUT

②V_{GG} : GATE BIAS SUPPLY

③V_{DD} : DRAIN BIAS SUPPLY

④P_O : RF OUTPUT

⑤GND: FIN

ABSOLUTE MAXIMUM RATINGS (T_c=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
V _{DD}	Supply voltage	V _{GG} ≤3.5V, Z _G =Z _L =50Ω	9.2	V
V _{GG}	Gate bias voltage		4	V
P _{in}	Input power	f=135-155MHz, Z _G =Z _L =50Ω	70	mW
P _O	Output power	f=135-155MHz, Z _G =Z _L =50Ω	10	W
T _{C (OP)}	Operation case temperature	f=135-155MHz, Z _G =Z _L =50Ω	-30 to +100	°C
T _{stg}	Storage temperature		-40 to +110	°C

Note. Above parameters are guaranteed independently.

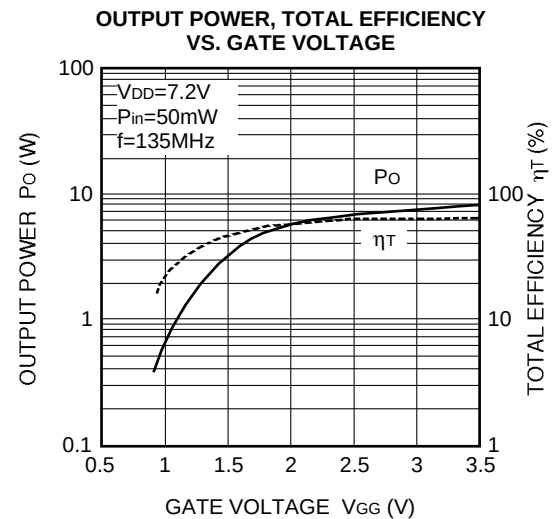
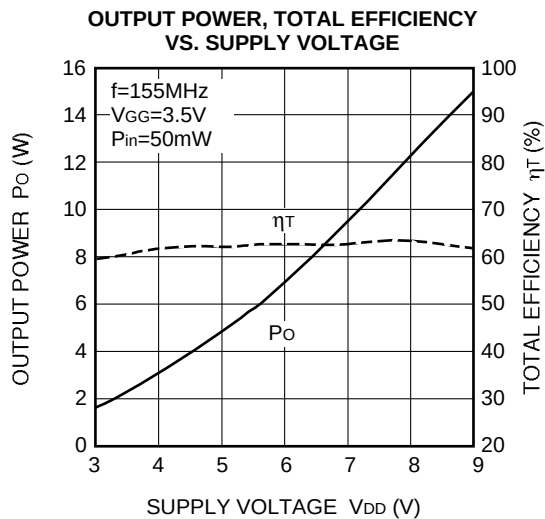
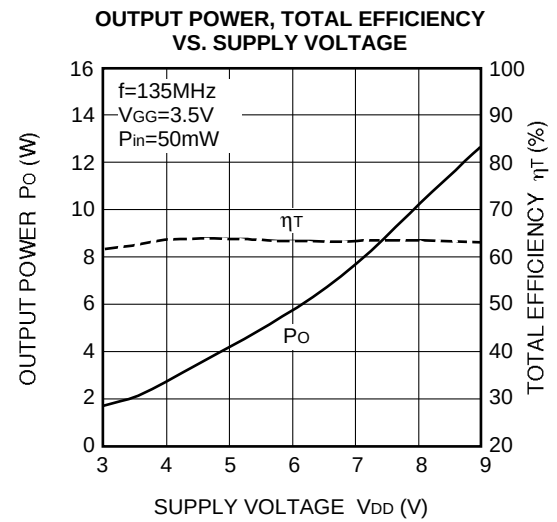
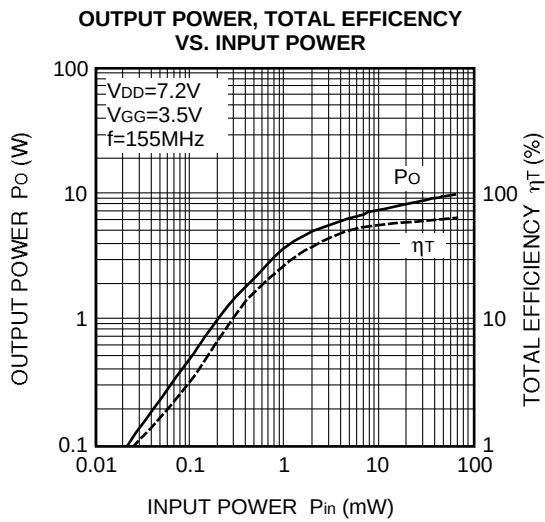
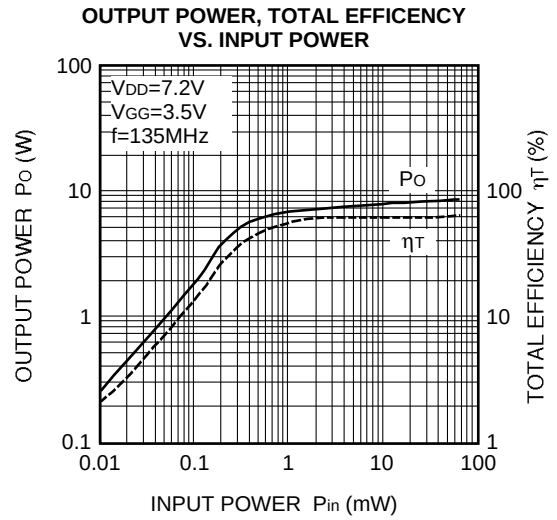
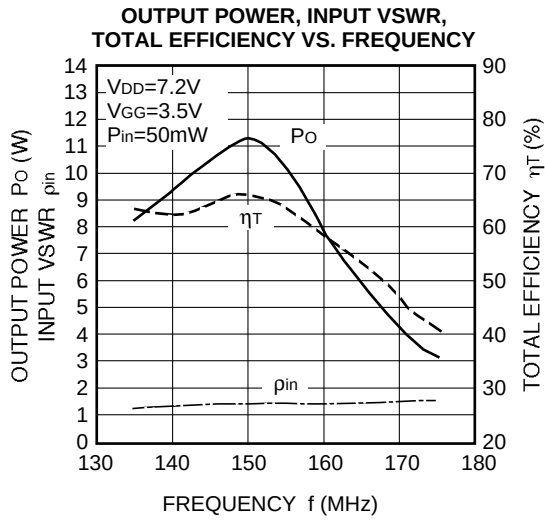
ELECTRICAL CHARACTERISTICS (T_c=25°C, Z_G=Z_L=50Ω unless otherwise noted)

Symbol	Parameter	Test conditions	Limits		Unit
			Min	Max	
f	Frequency range		135	155	MHz
P _O	Output power	V _{DD} =7.2V, V _{GG} =3.5V, P _{in} =50mW	7		W
η _T	Total efficiency		50		%
2f _o	2nd. harmonic			-20	dBc
ρ _{in}	Input VSWR			4	-
-	Stability	Z _G =50Ω, V _{DD} =4-9.2V, Load VSWR<4:1	No parasitic oscillation		-
-	Load VSWR tolerance	V _{DD} =9.2V, P _{in} =50mW, P _O =7W (V _{GG} adjust), Z _L =20:1	No degradation or destroy		-

Note. Above parameters, ratings, limits and test conditions are subject to change.

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TYPICAL PERFORMANCE DATA



SILICON MOS FET POWER AMPLIFIER, 135-155MHz, 7W, FM PORTABLE RADIO

